



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92S Plastic-Encapsulate Transistors

2SA1585S TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_D : 0.4W (T_{amb}=25^{\circ}C)$$

Collector current

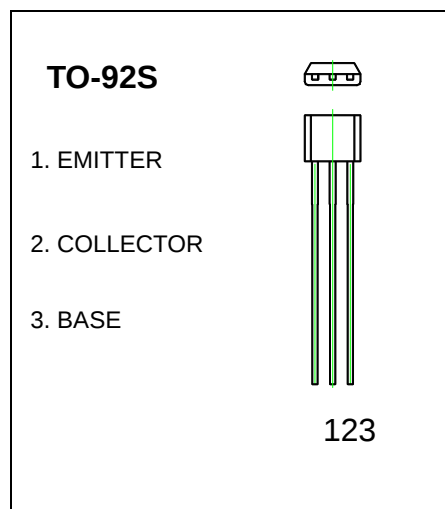
$$I_{CM} : -2A$$

Collector-base voltage

$$V_{(BR)CBO} : -20V$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^{\circ}C \text{ to } +150^{\circ}C$$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -0.1A$	120		390	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -2A, I_B = -0.1A$			-0.82	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -0.5A$ $F = 100MHz$	200			MHz

CLASSIFICATION OF h_{FE}

Rank	Q	R
Range	120-170	180-390